

# 74V2G00

## **DUAL 2-INPUT NAND GATE**

- HIGH SPEED:  $t_{PD} = 3.7 \text{ ns}$  (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:
   I<sub>CC</sub> = 1 μA (MAX.) at T<sub>A</sub> = 25 °C
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (MIN.)
- POWER DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |IOH| = IOL = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS: tplh ≅ tphl
- OPERATING VOLTAGE RANGE: V<sub>CC</sub> (OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

#### **DESCRIPTION**

The 74V2G00 is an advanced high-speed CMOS DUAL 2-INPUT NAND GATE fabricated with sub-micron silicon gate and double-layer metal



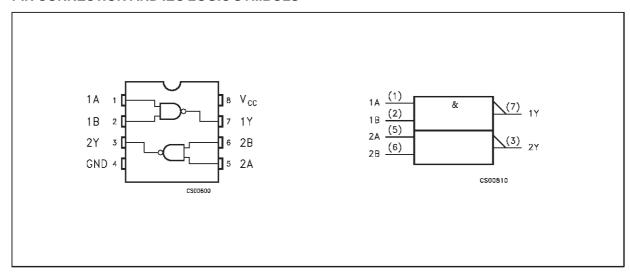
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SOT23-8L		74V2G00STR					

wiring C<sup>2</sup>MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

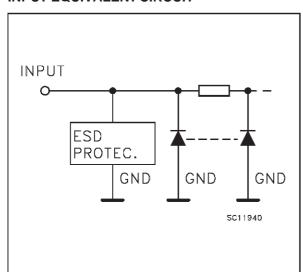
Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



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#### INPUT EQUIVALENT CIRCUIT



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	1A, 2A	Data Input
2, 6	1B, 2B	Data Input
7, 3	1Y, 2Y	Data Output
4	GND	Ground (0V)
8	Vcc	Positive Supply Voltage

#### **TRUTH TABLE**

Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 1)	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 2)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
lok	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	2.0 to 5.5	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage (see note 1)	0 to 5.5	V
Vo	Output Voltage (see note 2)	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 3) ( $V_{CC} = 3.3 \pm 0.3V$ ) ( $V_{CC} = 5.0 \pm 0.5V$ )	0 to 100 0 to 20	ns/V ns/V

<sup>1)</sup> Vcc = 0V

<sup>1)</sup>  $V_{CC} = 0V$ 

<sup>2)</sup> High or Low State

<sup>2)</sup> High or Low State 3) V<sub>IN</sub> from 30% to 70% of V<sub>CC</sub>

#### **DC SPECIFICATIONS**

Symbol	Parameter	Tes	t Conditions			Value			Unit
		Vcc		T,	T <sub>A</sub> = 25 °C		-40 to	85 °C	
		(V)		Min.	Тур.	Max.	Min.	Max.	
$V_{IH}$	High Level Input	2.0		1.5			1.5		V
	Voltage	3.0 to 5.5		0.7V <sub>CC</sub>			0.7V <sub>CC</sub>		V
VIL	Low Level Input	2.0				0.5		0.5	V
	Voltage	3.0 to 5.5				0.3V <sub>CC</sub>		0.3V <sub>CC</sub>	V
V <sub>OH</sub>	High Level Output	2.0	I <sub>O</sub> =-50 μA	1.9	2.0		1.9		
	Voltage	3.0	I <sub>O</sub> =-50 μA	2.9	3.0		2.9		.,
		4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		V
		3.0	I <sub>O</sub> =-4 mA	2.58			2.48		
		4.5	I <sub>O</sub> =-8 mA	3.94			3.8		
V <sub>OL</sub>	Low Level Output	2.0	I <sub>0</sub> =50 μA		0.0	0.1		0.1	
	Voltage	3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1	.,
		4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1	V
		3.0	I <sub>O</sub> =4 mA			0.36		0.44	
		4.5	I <sub>O</sub> =8 mA			0.36		0.44	
I <sub>I</sub>	Input Leakage Current	0 to 5.5	$V_I = 5.5V$ or GND			±0.1		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10	μΑ
I <sub>OPD</sub>	Output Leakage Current	0	V <sub>OUT</sub> = 5.5V			0.5		5.0	μΑ

### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3 \text{ ns}$ )

Symbol	Parameter	Test Condition \		Value	Unit				
		Vcc	C∟	T <sub>A</sub> = 25 °C		-40 to	85 °C		
		(V)	(pF)	Min.	Тур.	Max.	Min.	Max.	
t <sub>PLH</sub>	Propagation Delay	3.3 <sup>(*)</sup>	15		5.5	7.9	1.0	9.5	
t <sub>PHL</sub>	Time	3.3 <sup>(*)</sup>	50		8.0	11.4	1.0	13.0	ns
		5.0 <sup>(**)</sup>	15		3.7	5.5	1.0	6.5	
		5.0 <sup>(**)</sup>	50		5.2	7.5	1.0	8.5	

<sup>(\*)</sup> Voltage range is 3.3V ± 0.3V (\*\*) Voltage range is 5V ± 0.5V

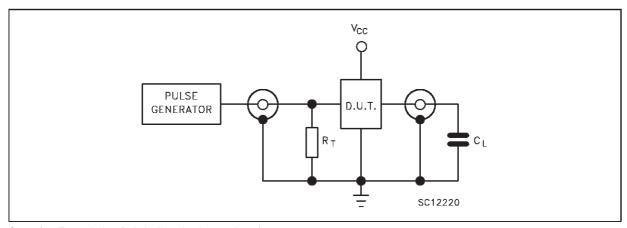
#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Value				Unit
			T,	T <sub>A</sub> = 25 °C		-40 to 85 °C		
			Min.	Тур.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			4	10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			19				pF

<sup>1)</sup> CPD is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/2$ 

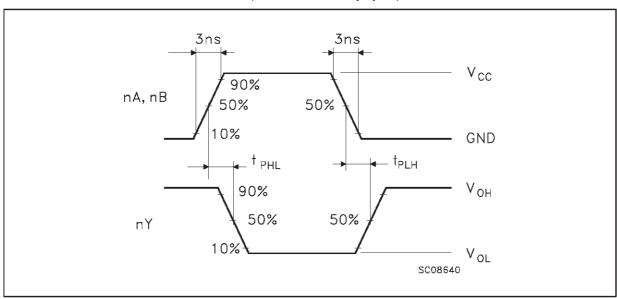


#### **TEST CIRCUIT**



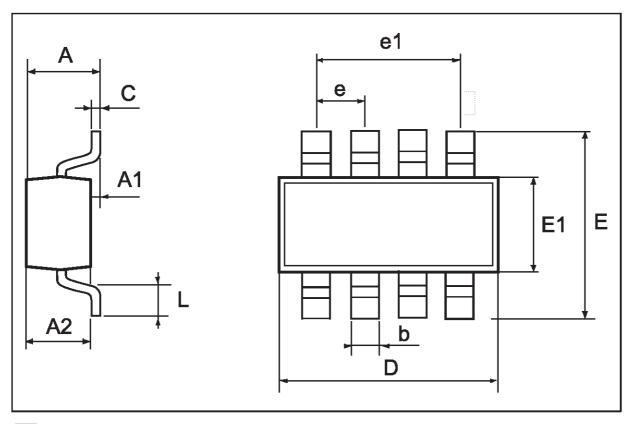
 $C_L$  = 15/50 pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically  $50\Omega)$ 

## WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



## **SOT23-8L MECHANICAL DATA**

DIM.		mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.15	0.0		5.9	
A2	0.90		1.30	35.4		51.2	
b	0.22		0.38	8.6		14.9	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	2.60		3.00	102.3		118.1	
E1	1.50		1.75	59.0		68.8	
L	0.35		0.55	13.8		21.6	
е		0.65			25.6		
e1		1.95			76.7		



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